



DMP2305U

P-CHANNEL ENHANCEMENT MODE MOSFET

Features

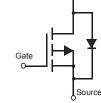
- Low On-Resistance
 - 60mΩ @ V_{GS} = -4.5V
 - 90mΩ @ V_{GS} = -2.5V
 - 113mΩ @ V_{GS} = -1.8V
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (approximate)

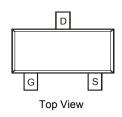


Top View



Drain

Internal Schematic



Ordering Information (Note 4&5)

Part Number	Qualification	Case	Packaging
DMP2305U-7	Standard	SOT23	3000/Tape & Reel
DMP2305UQ-7	Automotive	SOT23	3000/Tape & Reel

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

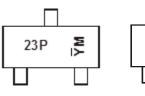
 See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_grade_definitions/

same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_grad 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html

Marking Information





23P = Product Type Marking Code YM = Date Code Marking for SAT (Shanghai Assembly/ Test site) $\overline{Y}M$ = Date Code Marking for CAT (Chengdu Assembly/ Test site) Y or \overline{Y} = Year (ex: A = 2013) M = Month (ex: 9 = September)

Chengdu A/T Site

Shanghai A/T Site

Date Code Key

Notes:

Date code noy												
Year	200	9	2010		2011	20	12	2013		2014	2	2015
Code	W		Х		Y	2	Ζ	А		В		С
-		· - ·						-				_
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characte	eristic		Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	-20	V
Gate-Source Voltage		V _{GSS}	±8	V	
Continuous Drain Current (Note 6)	Steady State	T _A = +25°C T _A = +70°C	۱ _D	-4.2 -3.4	А
Pulsed Drain Current (Note 7)		IDM	-10	А	

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	PD	1.4	W
Thermal Resistance, Junction to Ambient $@T_A = 25^{\circ}C$	R _{θJA}	90	°C/W
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

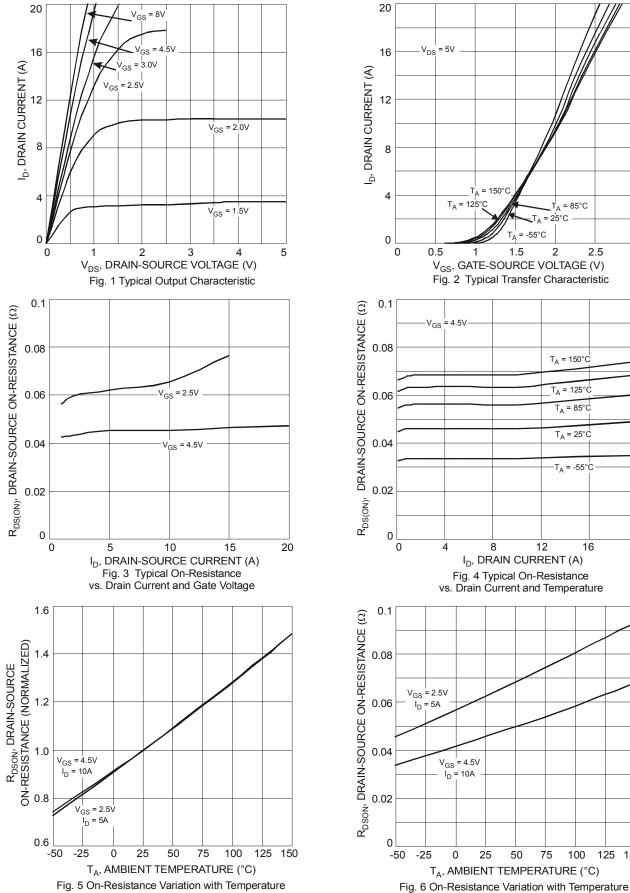
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Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 8)								
Drain-Source Breakdown Voltage	BV _{DSS}	-20			V	$V_{GS} = 0V, I_D = -250\mu A$		
Zero Gate Voltage Drain Current T _J = +25°C	IDSS	_		-1.0	μA	V_{DS} = -20V, V_{GS} = 0V		
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	V_{GS} = ±8V, V_{DS} = 0V		
ON CHARACTERISTICS (Note 8)								
Gate Threshold Voltage	V _{GS(th)}	-0.5	-	-0.9	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$		
			45	60		V _{GS} = -4.5V, I _D = -4.2A		
Static Drain-Source On-Resistance	R _{DS} (ON)		60	90	mΩ	V _{GS} = -2.5V, I _D = -3.4A		
			87	113		V _{GS} = -1.8V, I _D = -2.0A		
Forward Transfer Admittance	Y _{fs}	_	9		S	$V_{DS} = -5V, I_D = -4A$		
DYNAMIC CHARACTERISTICS (Note 9)						_		
Input Capacitance	Ciss	_	727		pF	N 00X X 0X		
Output Capacitance	Coss	_	69		pF	└V _{DS} = -20V, V _{GS} = 0V └f = 1.0MHz		
Reverse Transfer Capacitance	Crss	_	64		pF	1 - 1:000112		
Gate Resistance	R _G		23		Ω	$V_{GS} = 0V, V_{DS} = 0V, f = 1.0MHz$		
SWITCHING CHARACTERISTICS						_		
Total Gate Charge	Qg	_	7.6		nC			
Gate-Source Charge	Q _{gs}	_	1.4		nC	V_{GS} = -4.5V, V_{DS} = -4V, I_{D} = -3.5A		
Gate-Drain Charge	Q _{gd}	_	1.2		nC	7		
Turn-On Delay Time	t _{D(on)}	_	14.0		ns			
Turn-On Rise Time	t _r	_	13.0		ns	$V_{DS} = -4V, V_{GS} = -4.5V,$		
Turn-Off Delay Time	t _{D(off)}	_	53.8		ns	$R_L = 4\Omega, R_G = 6\Omega, I_D = -1A$		
Turn-Off Fall Time	t _f	_	23.2		ns			

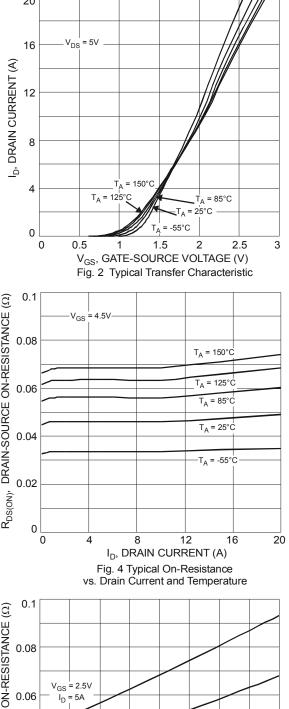
Notes:

6. Device mounted on FR-4 PCB with 2oz. Copper and test pulse width t \leq 10s.

Bevice induced of the rest pulse with limited by junction temperature.
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to production testing.







V_{GS} = 4.5V

I_D = 10A

0

25

50

T_A, AMBIENT TEMPERATURE (°C)

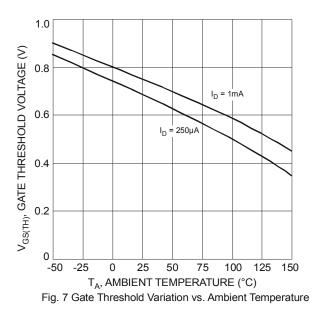
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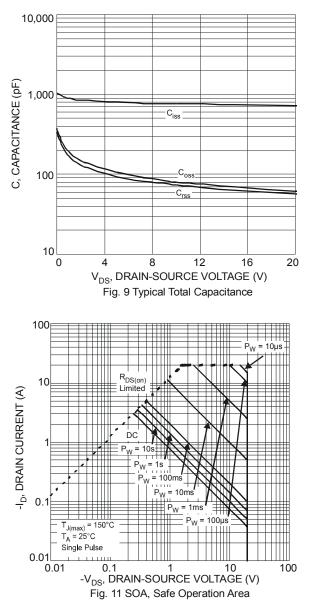
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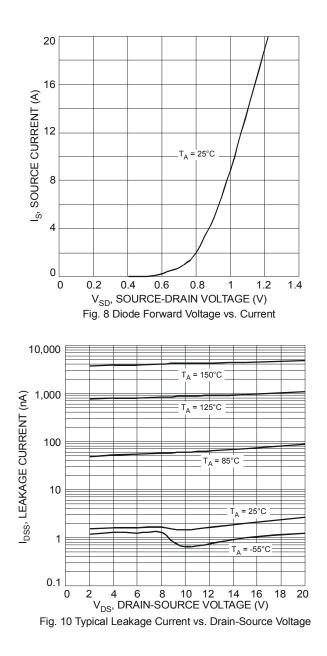


125 150

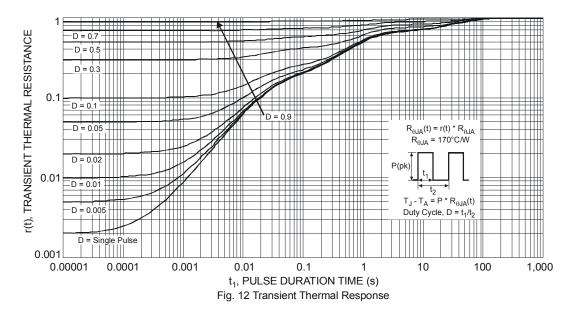






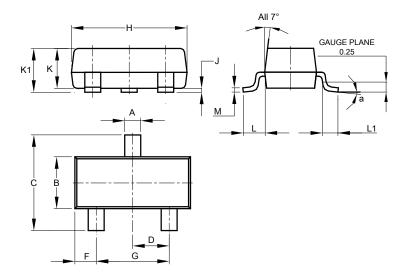






Package Outline Dimensions

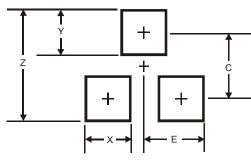
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



	SOT23							
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
В	1.20	1.40	1.30					
С	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
н	2.80	3.00	2.90					
J	0.013	0.10	0.05					
κ	0.890	1.00	0.975					
K1	0.903	1.10	1.025					
_	0.45	0.61	0.55					
L1	0.25	0.55	0.40					
Μ	0.085	0.150	0.110					
α	8°							
All	All Dimensions in mm							

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35



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